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(71) Applicant: **VERSUM MATERIALS US, LLC** [US/US];
8555 South River Parkway, Tempe, Arizona 85284 (US).

(72) Inventors: **LEI, Xinjian**; c/o Versum Materials US, LLC,
8555 South River Parkway, Tempe, Arizona 85284 (US).
LI, Ming; c/o Versum Materials US, LLC, 8555 South River
Parkway, Tempe, Arizona 85284 (US). **MACDONALD,**
Matthew R.; c/o Versum Materials US, LLC, 8555 South
River Parkway, Tempe, Arizona 85284 (US). **WANG,**
Meiliang; c/o Versum Materials US, LLC, 8555 South River
Parkway, Tempe, Arizona 85284 (US).

(74) Agent: **BENSON, David K.**; Versum Materials US, LLC,
7350 Tilghman Street, Suite 104, Allentown, Pennsylvania
18106 (US).

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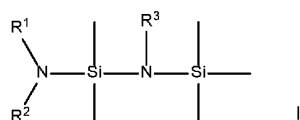
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(54) Title: ORGANOAMINODISILAZANES FOR HIGH TEMPERATURE ATOMIC LAYER DEPOSITION OF SILICON OXIDE THIN FILMS



(57) Abstract: An atomic layer deposition (ALD) process for formation of silicon oxide at a temperature greater than 500 °C is performed using at least one organoaminodisilazane precursor having the following Formula I: wherein R¹ and R² are each independently selected from hydrogen, a linear or branched C₁ to C₁₀ alkyl group, and a C₆ to C₁₀ aryl group with a proviso that R¹ and R² cannot be both hydrogen; R³ is selected from hydrogen, a linear or branched C₁ to C₁₀ alkyl group, and a C₆ to C₁₀ aryl group; and either R¹ and R² are linked to form a cyclic ring structure or R¹ and R² are not linked to form a cyclic ring structure.

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